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## SPECIFICATION AMENDMENTS

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[0078] Field-effect transistors 125, 127, 129, and 131 can be all N-channel devices which are smaller, less expensive, have lower "on" resistance, and are more plentiful on the market than P-channel devices. In order to accommodate the N-channel devices, the gates would be coupled to level shifters 115, 116, 117, and 118 by transformers like the ones shown in Figs. 3 and 4. It is possible to generate less sophisticated driving signals with a single transformer having one primary winding and four secondary windings, one for each transistor gate. One level shifter would be used to drive the primary winding of the transformer.

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